TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

GT50N322A

Voltage Resonance Inverter Switching Application Fifth Generation IGBT

· FRD included between emitter and collector

• Enhancement mode type

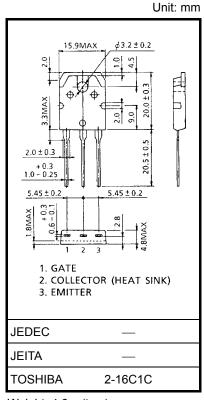
• High speed IGBT : $t_f = 0.10 \mu s$ (typ.) ($I_C = 60 A$)

FRD : $t_{rr} = 0.8 \mu s$ (typ.) (di/dt = -20 A/ μs)

Low saturation voltage: V_{CE} (sat) = 2.2 V (typ.) (I_C = 60 A)

Absolute Maximum Ratings (Ta = 25°C)

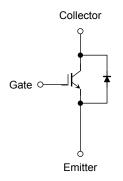
Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	1000	V	
Gate-emitter voltage		V _{GES}	± 25	V	
Collector current	DC	IC	50	А	
	1ms	I _{CP}	120		
Diode forward current	DC	lF	15	Α	
	1ms	I _{FP}	120		
Collector power dissipation ($Tc = 25^{\circ}C$)		P _C	156	W	
Junction temperature		Tj	150	°C	
Storage temperature		T _{stg}	-55 to 150	°C	



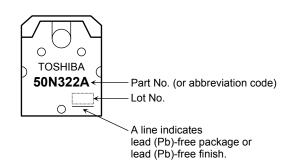
Weight: 4.6 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Equivalent Circuit



Marking

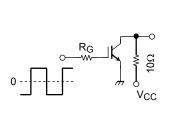


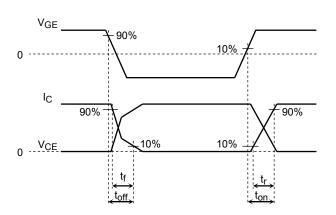
Electrical Characteristics (Ta = 25°C)

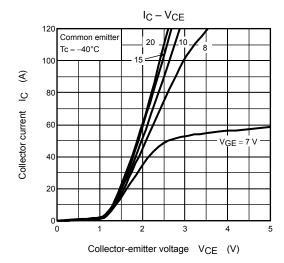
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I _{GES}	$V_{GE} = \pm 25 \text{ V}, V_{CE} = 0$	_	_	± 500	nA
Collector cut-off current		I _{CES}	V _{CE} = 1000 V, V _{GE} = 0	_	_	1.0	mA
Gate-emitter cut-off voltage		V _{GE} (OFF)	$I_C = 60 \text{ mA}, V_{CE} = 5 \text{ V}$	3.0	_	6.0	V
Collector-emitter saturation voltage		V _{CE} (sat)	I _C = 60 A, V _{GE} = 15 V	_	2.2	2.8	V
Input capacitance		C _{ies}	V _{CE} = 10 V, V _{GE} = 0, f = 1 MHz	_	4000	_	pF
Switching time	Rise time	t _r	Resistive Load	_	0.23	_	μs
	Turn-on time	t _{on}	V _{CC} = 600 V, I _C = 60 A	_	0.33	_	
	Fall time	t _f	$V_{GG} = \pm 15 \text{ V}, R_G = 51 \Omega$	_	0.10	0.25	
	Turn-off time	t _{off}	(Note 1)	_	0.70	_	
Diode forward voltage		V _F	I _F = 15 A, V _{GE} = 0	_	1.2	1.9	V
Reverse recovery time		t _{rr}	$I_F = 15 \text{ A}, V_{GE} = 0, di/dt = -20 \text{ A/}\mu\text{s}$	_	0.8	_	μs
Thermal Resistance R		Rth(j-c)	_	_	_	0.8	°C/W
Thermal Resistance		Rth(j-c)	_	_	_	4.0	°C/W

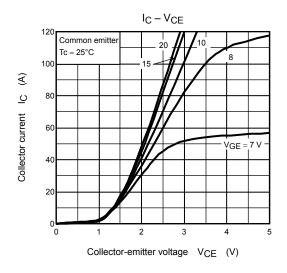
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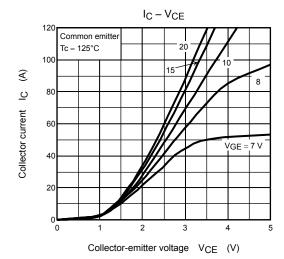
Note 1: Switching time measurement circuit and input/output waveforms

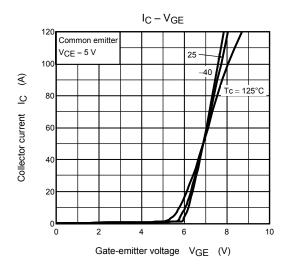


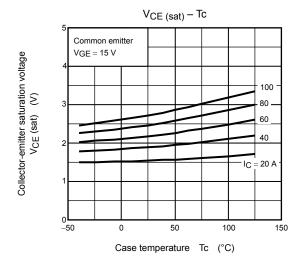


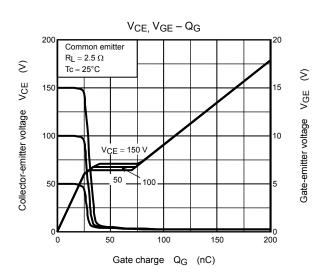


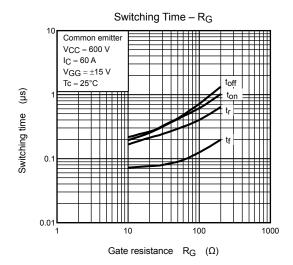


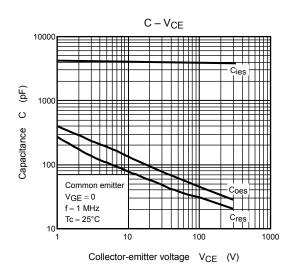


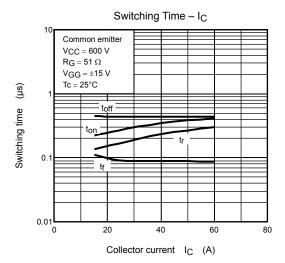


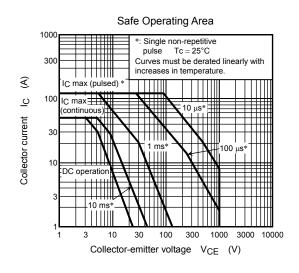


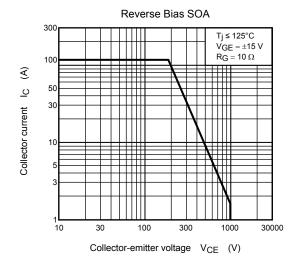


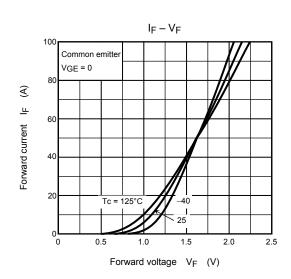


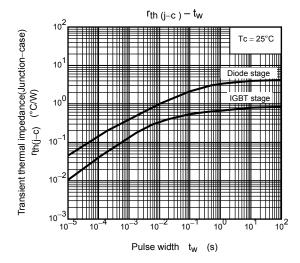


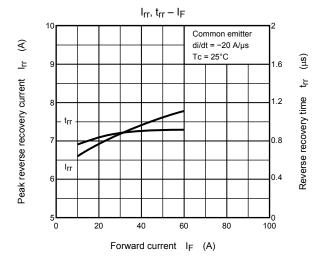


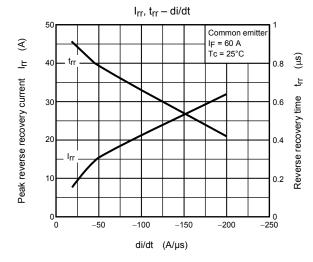












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